



(10) **Patent Number:** US RE45,732 E
(45) **Date of Reissued Patent:** Oct. 6, 2015

- (56)
- References Cited**

- U.S. PATENT DOCUMENTS

- JP 2007-266143 10/2007

- ## OTHER PUBLICATIONS

Korean Office Action issued on Jan. 24, 2011 in corresponding Korean Application No. 10-2009-48724 (with an English Translation).

* cited by examiner

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(57) **ABSTRACT**

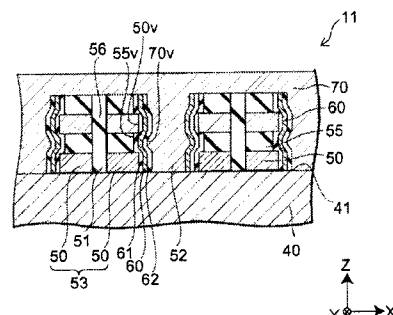
- A nonvolatile semiconductor storage device includes: a plurality of stacked units juxtaposed on a major surface of a substrate, each stacked unit aligning in a first direction parallel to the major surface of the substrate; and a gate electrode aligning parallel to the major surface in a second direction non-parallel to the first direction. Each of the plurality of stacked units includes a plurality of stacked semiconductor layers via an insulating layer. The plurality of stacked units are juxtaposed so that the spacings between adjacent stacked units are alternately a first spacing and a second spacing larger than the first spacing. The second spacing is provided at a periodic interval four times a size of a half pitch F of the bit line. The gate electrode includes a protruding portion that enters into a gap of the second spacing between the stacked units. A first insulating film, a charge storage layer, and a second insulating film are provided between a side face of the semiconductor layer and the protruding portion.

5 Claims, 13 Drawing Sheets

- (51) **Int. Cl.**
H01L 21/22 (2006.01)
H01L 27/15 (2006.01)

- (52) **U.S. Cl.**
CPC **H01L 27/11582** (2013.01); **H01L 27/11573**
(2013.01); **H01L 27/11578** (2013.01)

- (58) **Field of Classification Search**
CPC H01L 27/11573; H01L 27/11578;
H01L 27/11582
USPC 438/591; 257/E27.078
See application file for complete search history.



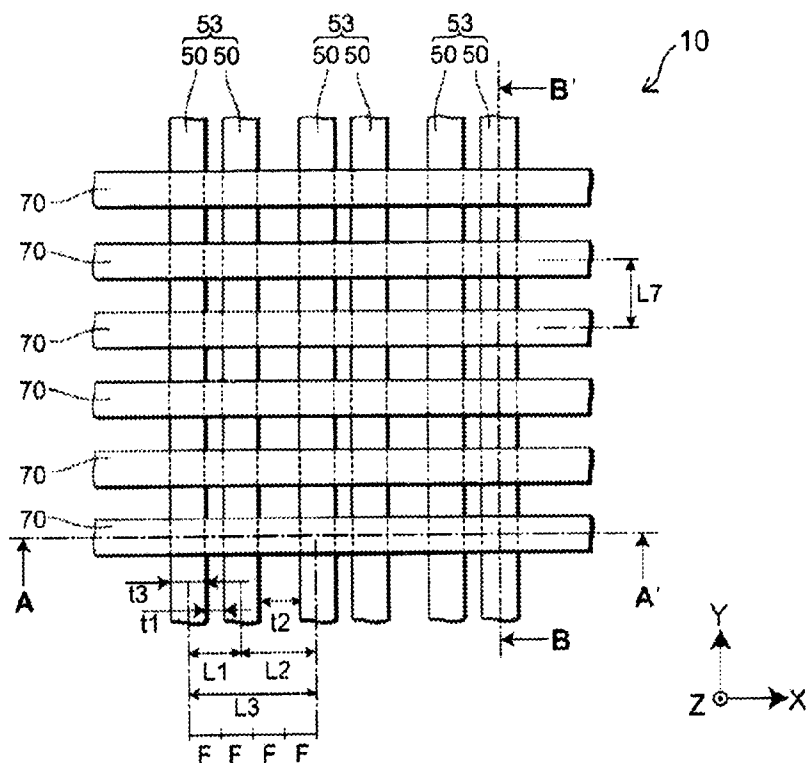


FIG. 1A

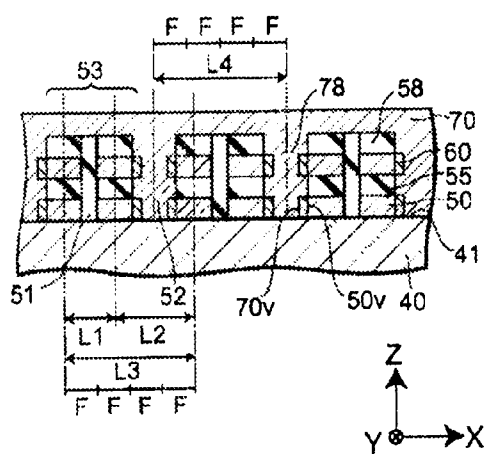


FIG. 1B

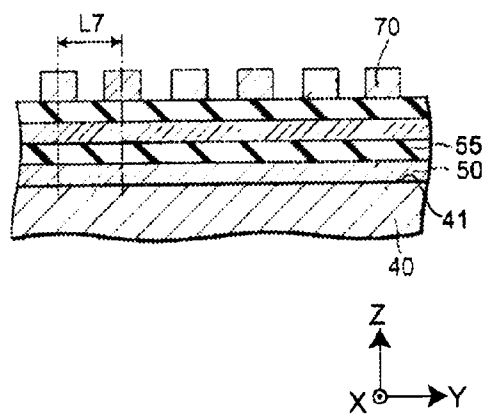


FIG. 1C

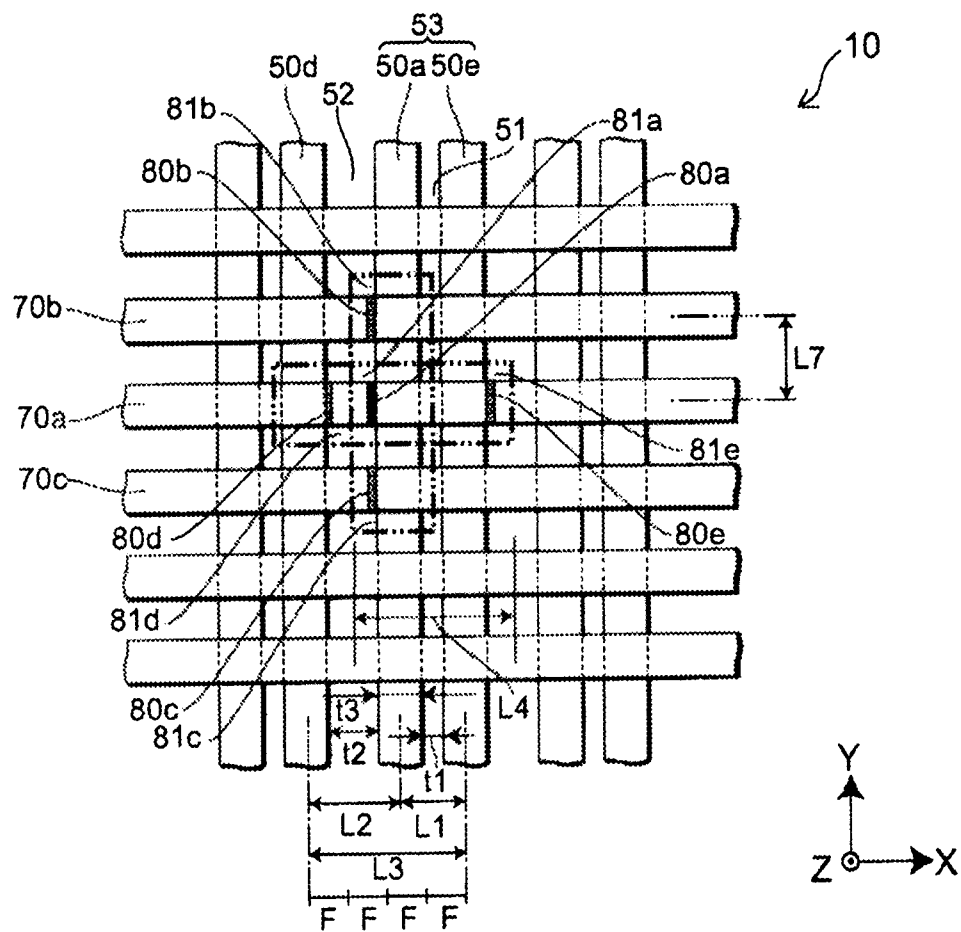


FIG. 2

FIG. 3A

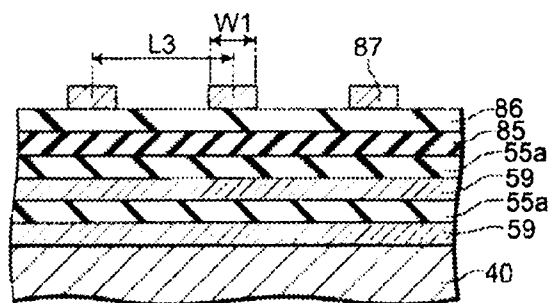


FIG. 3B

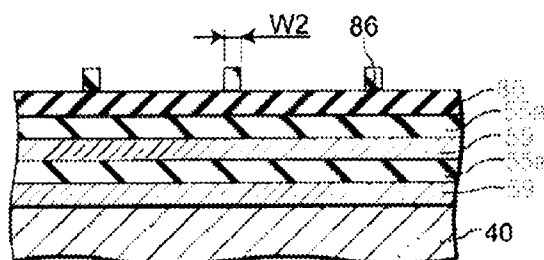


FIG. 3C

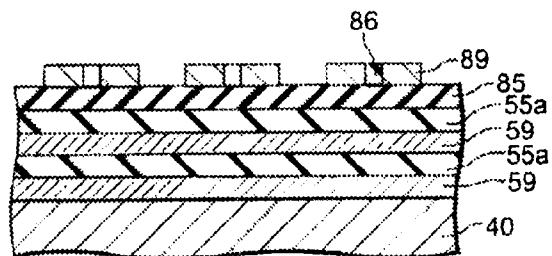


FIG. 3D

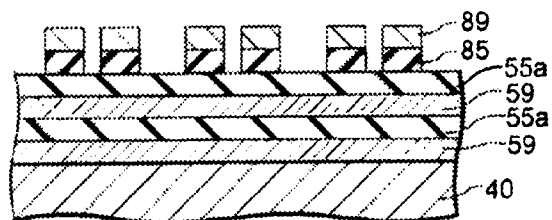


FIG. 3E

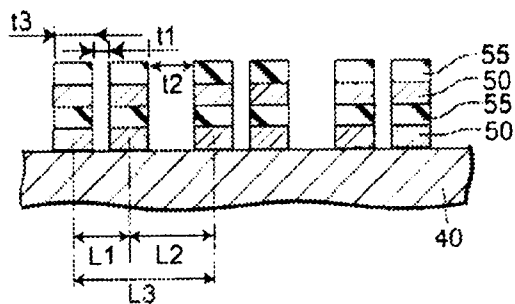


FIG. 4A

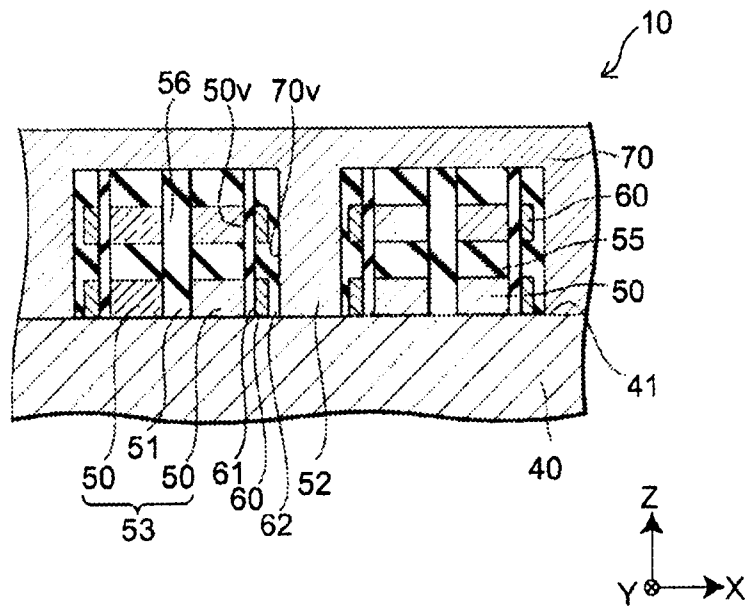
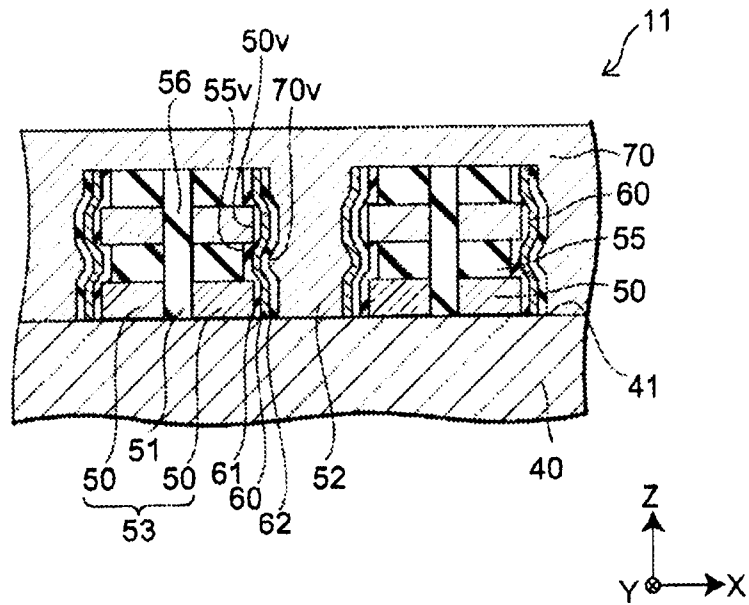


FIG. 4B



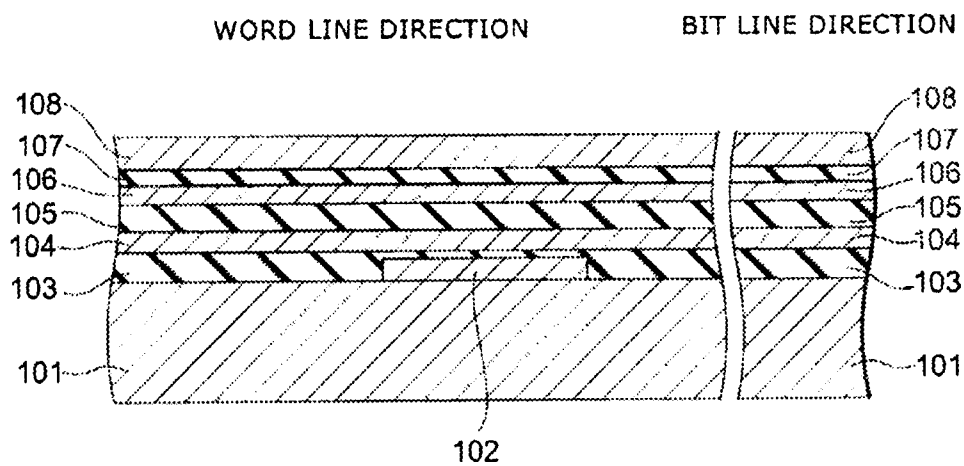


FIG. 5A

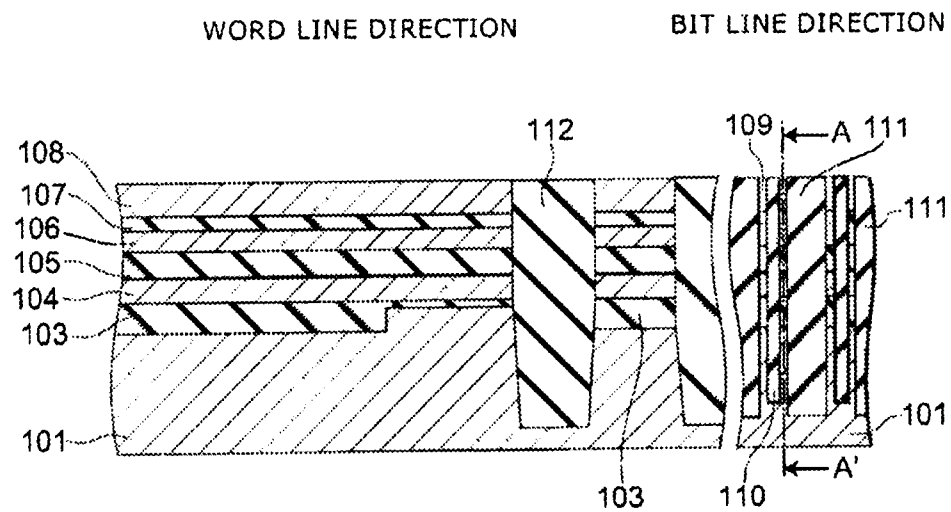


FIG. 5B

FIG. 6B

FIG. 7A

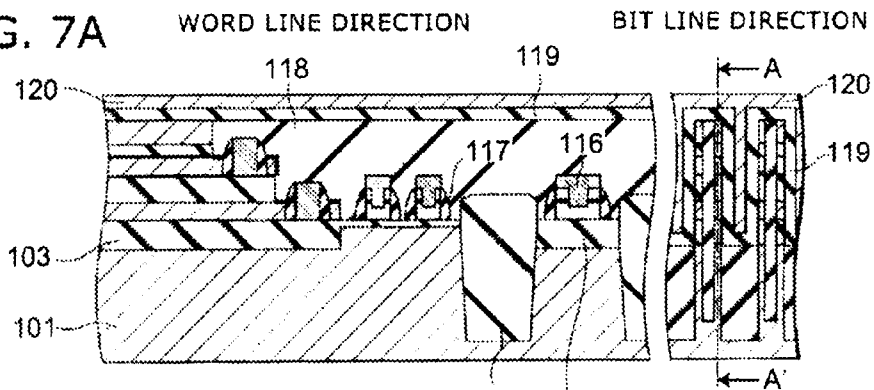


FIG. 7B

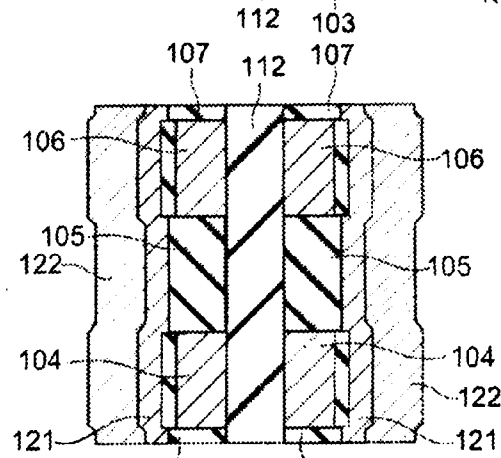
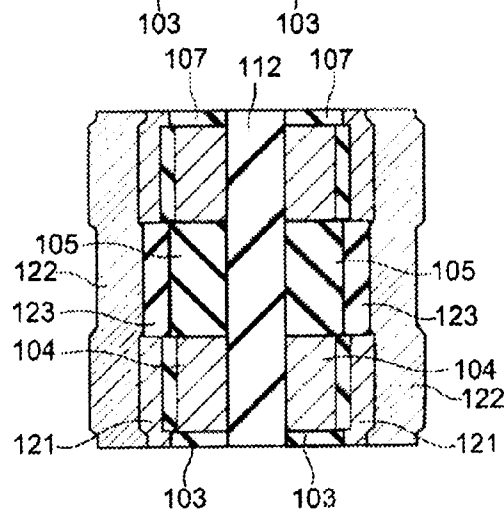


FIG. 7C



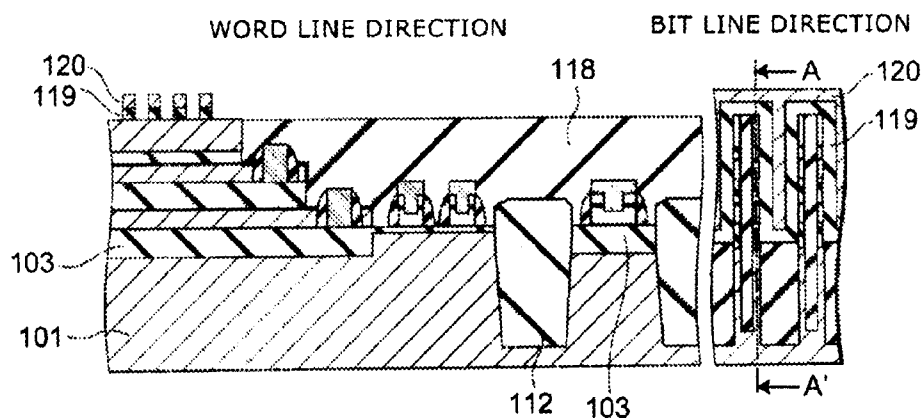


FIG. 8A

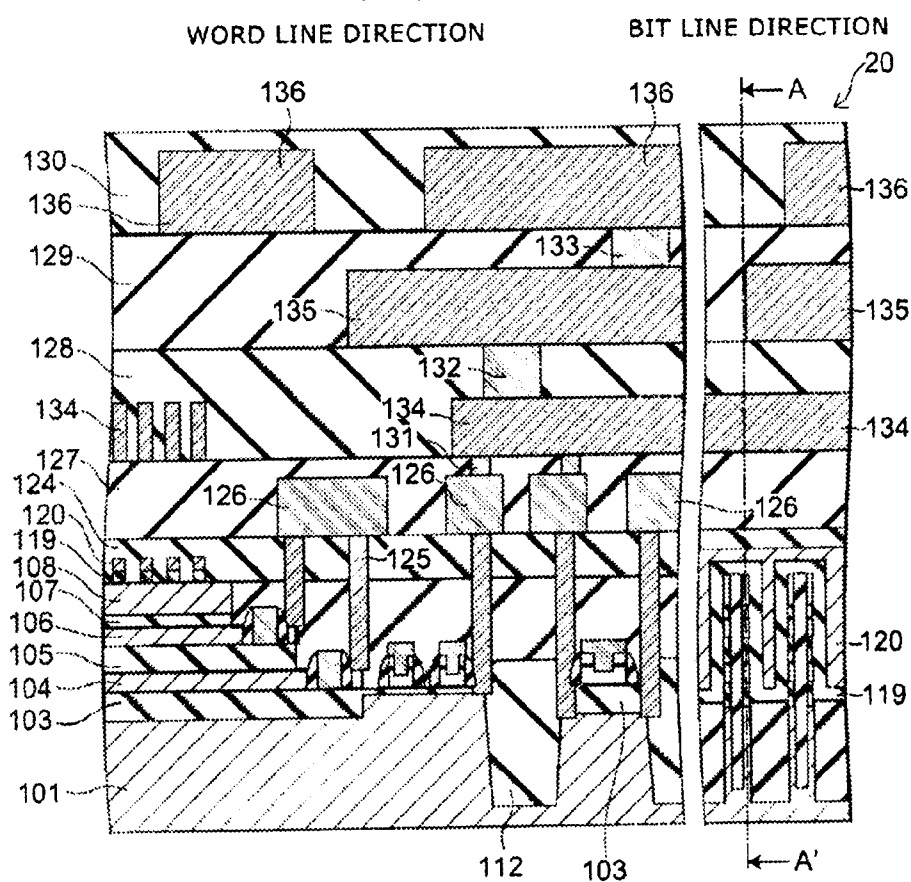


FIG. 8B

FIG. 9A

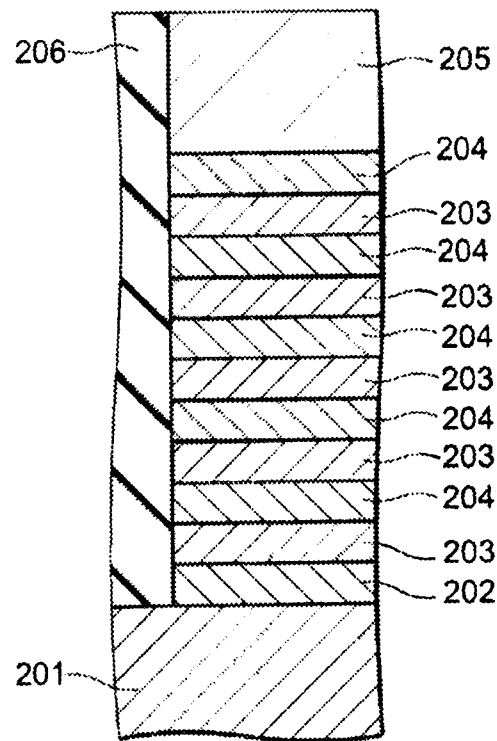


FIG. 9B

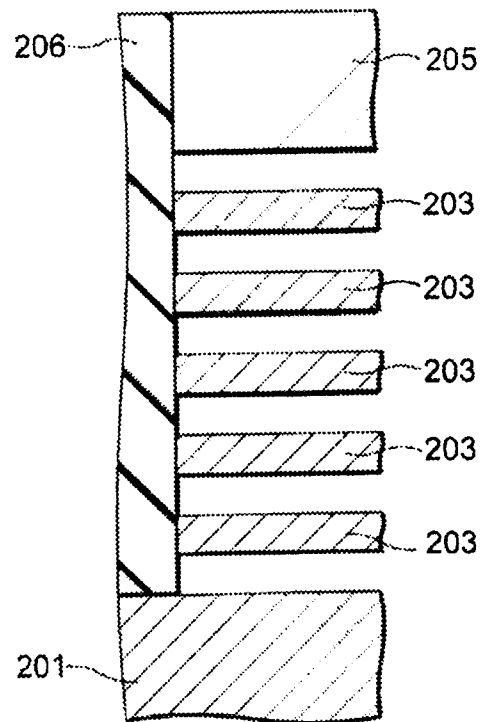


FIG. 10A

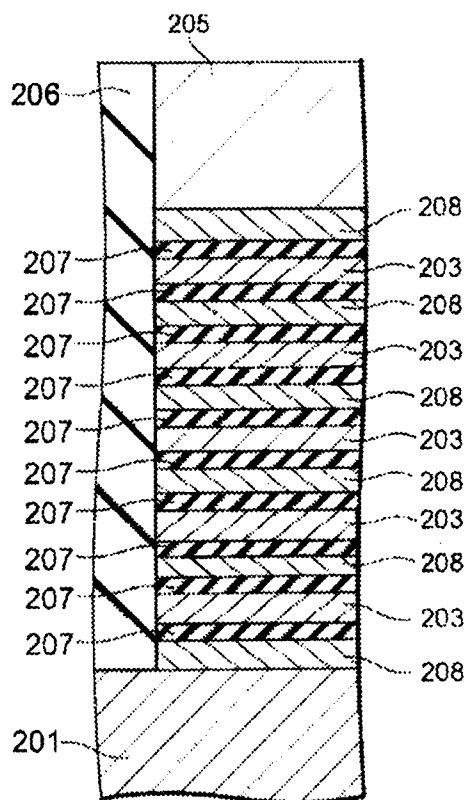


FIG. 10B

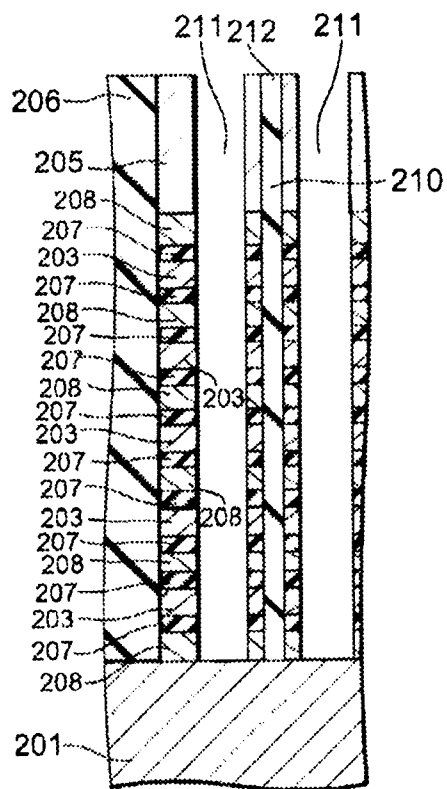


FIG. 11A

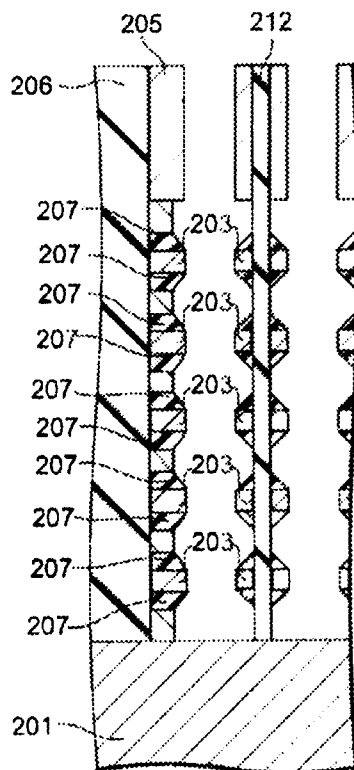
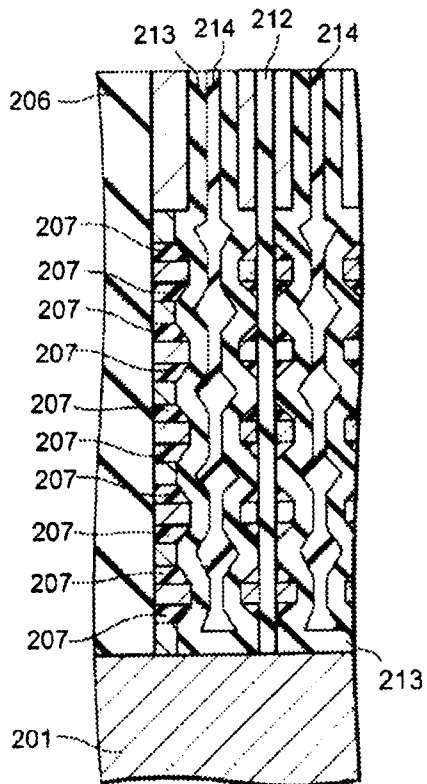


FIG. 11B



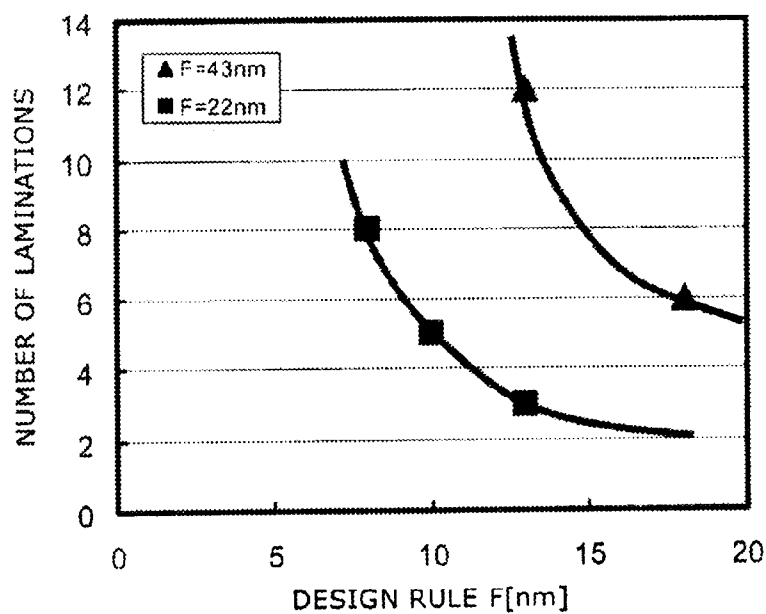


FIG. 12

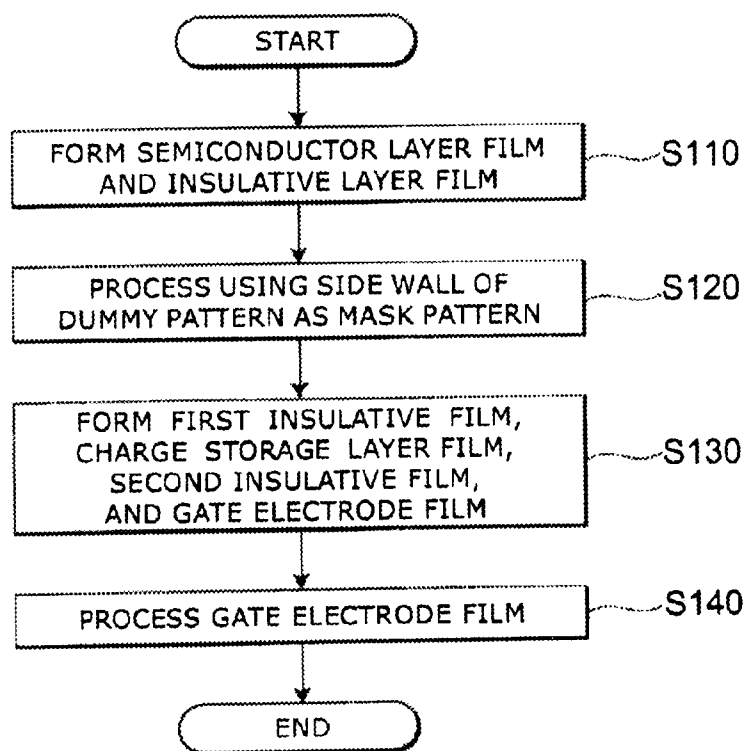


FIG. 13

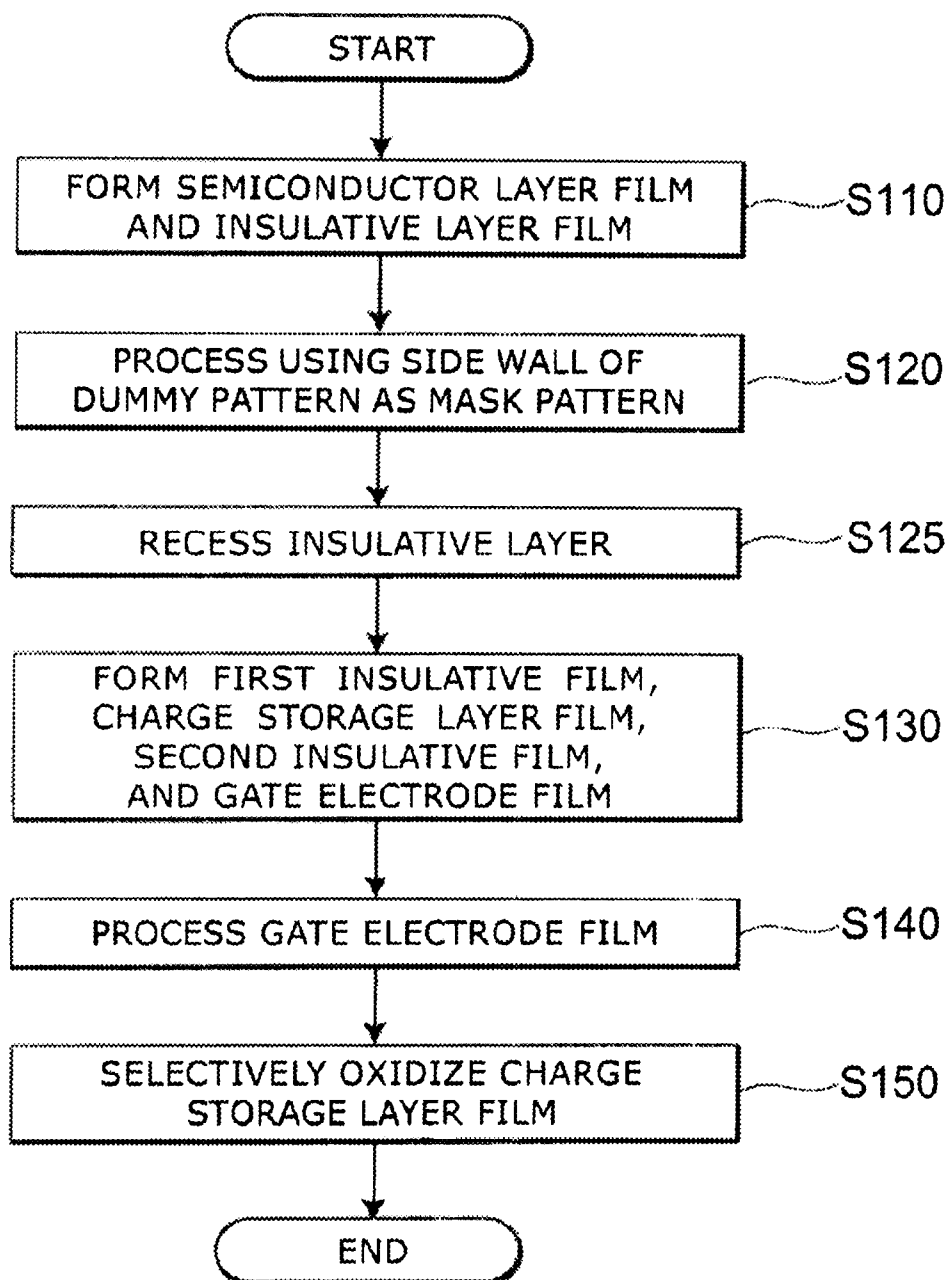


FIG. 14

1

NONVOLATILE SEMICONDUCTOR STORAGE DEVICE AND METHOD FOR MANUFACTURING SAME

Matter enclosed in heavy brackets [] appears in the original patent but forms no part of this reissue specification; matter printed in *italics* indicates the additions made by reissue; a claim printed with ~~strikethrough~~ indicates that the claim was canceled, disclaimed, or held invalid by a prior post-patent action or proceeding.

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is a *reissue application of U.S. Pat. No. 8,124,514, which is a divisional of U.S. application Ser. No. 12/476,799 filed Jun. 2, 2009 (now U.S. Pat. No. 7,851,849), and is based upon and claims the benefits of priority from the prior Japanese Patent Application No. 2008-146188, filed on Jun. 3, 2008; the entire contents of each of which are incorporated herein by reference.*

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a nonvolatile semiconductor storage device and a method for manufacturing the same.

2. Background Art

Nonvolatile memory typified by NAND flash memory is used widely for large-capacity data storage in mobile telephones, digital still cameras, USB memory, silicon audio, and the like. The market continues to grow due to the reduction of manufacturing costs per bit enabled by rapid downscaling. NAND flash memory in particular has a small cell surface area of $4F^2$, where F is the minimum processing dimension (the half pitch); and rapid downscaling due to the simple structure thereof is progressing. However, bit density increase of future NAND flash memory will face many issues such as limitations on the downscaling of lithography, reduced reliability due to the transistor scaling, increased fluctuation of the transistor characteristics accompanying the transistor size downscaling, limitations on operation speed due to negative effects of downscaling such as short channel effects or narrow channel effects, and so on.

Conversely, P-A 2007-266143 (Kokai) discusses technology relating to a nonvolatile semiconductor storage device in which insulating films and charge storage layers are provided around a semiconductor of a columnar configuration, and multiple recording layers are stacked. However, in the case of this structure, it is necessary to pattern the gate electrode that selects the charge storage layer into a striped configuration in a plane parallel to the substrate. Therefore, the cell surface area thereof is $6F^2$ as compared to the cell surface area of normal NAND flash memory of $4F^2$ (where F is the half pitch). Further, in the case of the structure of P-A 2007-266143 (Kokai), downscaling is constrained by manufacturing process constraints when forming a silicon plug after forming the gate electrode. Then, forming the silicon plug after the gate electrode formation constrains the materials used in the gate electrode; and it is difficult to reduce the resistance. Therefore, it is necessary to make the gate electrode thick or increase the space between adjacent cells to prevent the depletion of the electrode. Thereby, downscaling is constrained. Moreover, an operation mechanism is different than that of NAND flash memory. Therefore, conven-

2

tional peripheral circuit configurations of NAND flash memory will be re-designed before diversion

SUMMARY OF THE INVENTION

According to an aspect of the invention, there is provided a nonvolatile semiconductor storage device including: a substrate; a plurality of stacked units juxtaposed on a major surface of the substrate, each stacked unit aligning in a first direction parallel to the major surface of the substrate; a gate electrode aligning parallel to the major surface in a second direction non-parallel to the first direction; a charge storage layer; a first insulating film; and a second insulating film, each of the plurality of stacked units including a plurality of stacked semiconductor layers via an insulating layer, spacings between adjacent stacked units having a first spacing and a second spacing larger than the first spacing, the first spacing and the second spacing being alternately provided, the second spacing being provided at a periodic interval four times a size of a half pitch F of the bit line of the device, the gate electrode including a protruding portion entering into a gap between the stacked units, the gap having the second spacing, the charge storage layer being provided between a side face of the semiconductor layer and the protruding portion, the first insulating film being provided between the side face of the semiconductor layer and the charge storage layer, and the second insulating film being provided between the charge storage layer and the protruding portion.

According to another aspect of the invention, there is provided a method for manufacturing a nonvolatile semiconductor storage device, the device including: a semiconductor layer; a gate electrode provided facing the semiconductor layer; a charge storage layer provided between the semiconductor layer and the gate electrode; a first insulating film provided between the semiconductor layer and the charge storage layer; and a second insulating film provided between the charge storage layer and the gate electrode, the method including: stacking to form a semiconductor layer film and an insulating layer film on a major surface of a substrate, the semiconductor layer film forming the semiconductor layer, the insulating layer film forming an insulating layer; processing the semiconductor layer film and the insulating layer film to alternately provide a first spacing and a second spacing larger than the first spacing between stacked units, by using a side wall as a mask pattern, the side wall being formed on a side face of a dummy pattern formed at a period four times a size of a half pitch F of the bit line of the device, the side wall aligning in a first direction parallel to the major surface, the stacked units including the semiconductor layer and the insulating layer; forming a film forming the first insulating film, a film forming the charge storage layer, and a film forming the second insulating film on a side face of the stacked unit on the second spacing side, and further forming a gate electrode film forming the gate electrode on the film forming the second insulating film and on a major surface of the stacked unit; and processing the gate electrode film into a band configuration aligning in a second direction parallel to the major surface and non-parallel to the first direction.

BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1A to 1C are schematic views illustrating a configuration of a nonvolatile semiconductor storage device according to a first embodiment of the present invention;

FIG. 2 is a schematic plan view illustrating the half pitch of the nonvolatile semiconductor storage device according to the first embodiment of the present invention;

3

FIGS. 3A to 3E are schematic cross-sectional views in order of the steps, illustrating main components of a method for manufacturing the nonvolatile semiconductor storage device according to the first embodiment of the present invention;

FIGS. 4A and 4B are schematic cross-sectional views illustrating structures of main components of the nonvolatile semiconductor storage device according to the first embodiment of the present invention;

FIGS. 5A and 5B are schematic cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor storage device according to a first example of the first embodiment of the present invention;

FIGS. 6A and 6B are schematic cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor storage device according to the first example;

FIGS. 7A to 7C are views schematic cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor storage device according to the first example;

FIGS. 8A and 8B are views schematic cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor storage device according to the first example;

FIGS. 9A and 9B are schematic cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor storage device according to a second example of the first embodiment of the present invention;

FIGS. 10A and 10B are schematic cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor storage device according to the second example;

FIGS. 11A and 11B are schematic cross-sectional views illustrating a method for manufacturing a nonvolatile semiconductor storage device according to the second example;

FIG. 12 is a graph illustrating characteristics of a nonvolatile semiconductor storage device according to an embodiment of the present invention;

FIG. 13 is a flowchart illustrating a method for manufacturing a nonvolatile semiconductor storage device according to a second embodiment of the present invention; and

FIG. 14 is a flowchart illustrating a method for manufacturing a nonvolatile semiconductor storage device according to a third embodiment of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

Embodiments of the present invention will now be described in detail with reference to the drawings.

The drawings are schematic or conceptual; and the relationships between the thickness and width of portions, the proportions of sizes among portions, etc., are not necessarily the same as the actual values thereof. Further, the dimensions and proportions may be illustrated differently among drawings, even for identical portions.

In the specification and drawings, components similar to those described in regard to a drawing thereinabove are marked with like reference numerals, and a detailed description is omitted as appropriate.

First Embodiment

FIGS. 1A to 1C are schematic views illustrating a configuration of a nonvolatile semiconductor storage device according to a first embodiment of the present invention.

That is, FIG. 1A is a plan view, FIG. 1B is a cross-sectional view along line A-A' of FIG. 1A, and FIG. 1C is a cross-sectional view along line B-B' of FIG. 1A.

As illustrated in FIGS. 1A to 1C, a nonvolatile semiconductor storage device 10 according to the first embodiment of

4

the present invention includes a semiconductor layer 50, a gate electrode 70 provided to face the semiconductor layer 50, a charge storage layer 60 provided between the semiconductor layer 50 and the gate electrode 70, a first insulating film (not illustrated) provided between the semiconductor layer 50 and the charge storage layer 60, and a second insulating film (not illustrated) provided between the charge storage layer 60 and the gate electrode 70. In other words, the nonvolatile semiconductor storage device 10 is a memory including a MONOS (Metal Oxide Nitride Oxide Semiconductor) structure.

The semiconductor layer 50 aligns in a first direction (for example, an X-axis direction) parallel to a major surface 41 of a substrate 40, is multiply stacked on the substrate 40 via an insulating layer 55, and is multiply provided in a plane parallel to the major surface 41 with a spacing therebetween alternately arranged to be a first spacing 51 and a second spacing 52 larger than the first spacing 51.

The second spacing 52 is arranged at a period L4 which is four times the size of a half pitch F of the bit line of the nonvolatile semiconductor storage device 10. The half pitch F is described below.

Such a configuration can be formed by using a mask pattern formed by a side wall formed on a side face of a dummy pattern formed at a period four times the size of the half pitch F, and alternately arranging the spacing of the semiconductor layers 50 to be the first spacing 51 and the second spacing 52 which is larger than the first spacing 51. A method for forming the first spacing 51 and the second spacing 52 by utilizing the side wall is described below.

On the other hand, the gate electrode 70 is provided parallel to the major surface 41 to align in a second direction (for example, a Y-axis direction) non-parallel to the first direction (the X-axis direction). A portion of the gate electrode 70 enters into the second spacing 52 side of the semiconductor layers 50 to form a protruding portion 78. The gate electrode 70 has a single period, that is, is arranged at a distance L7. For example, the distance L7 may be twice the size of the half pitch F. In other words, the gate electrode 70 is arranged, for example, at a period twice the size of the half pitch F of the word line of the device.

The charge storage layer 60 is provided between a face 50v of the semiconductor layer 50 on the second spacing 52 side perpendicular to the major surface 41 and a face 70v of the gate electrode 70 perpendicular to the major surface 41.

As illustrated in FIGS. 1A to 1C, a Z axis is a direction perpendicular to the major surface 41 of the substrate 40; the X axis is an axis perpendicular to the Z axis; and the Y axis is a direction perpendicular to the Z axis and the X axis.

In this example, the stacked semiconductor layers 50 are multiply provided in the X-axis direction and align in band configurations. The spacing between the semiconductor layers 50 includes a narrow portion (the first spacing 51) and a wide portion (the second spacing 52). The gate electrode 70 aligns to intersect with the semiconductor layer 50. The first insulating film, the charge storage layer 60, and the second insulating film are provided between a side face of the semiconductor layer 50 and a side face of the gate electrode 70. In other words, the charge storage layers 60 which form memory cells (also referred to as "cells") of the nonvolatile semiconductor storage device 10 are stacked in both the direction perpendicular to the major surface 41 of the substrate 40 and directions parallel thereto.

In other words, the nonvolatile semiconductor storage device 10 according to this embodiment includes the substrate 40, the multiple stacked units 58 juxtaposed on the major surface 41 of the substrate 40 such that each aligns in

5

the first direction parallel to the major surface **41** of the substrate **40**, and the gate electrode **70** aligning parallel to the major surface **41** in the second direction non-parallel to the first direction. Each of the multiple stacked units **58** includes multiple semiconductor layers **50** stacked via the insulating layer **55**. The multiple stacked units **58** are juxtaposed such that the spacing between adjacent stacked units **58** is alternately provided as the first spacing **51** and the second spacing **52** which is larger than the first spacing **51**. The second spacing **52** is provided at a periodic interval four times the size of the half pitch F of the bit line of the nonvolatile semiconductor storage device **10**. The gate electrode **70** includes the protruding portion **78** which enters into the gap of the second spacing **52** between the stacked units **58**. The nonvolatile semiconductor storage device **10** further includes the charge storage layer **60** provided between the side face **50v** of the semiconductor layer **50** and the protruding portion **78**, the first insulating film (not illustrated) provided between the side face **50v** of the semiconductor layer **50** and the charge storage layer **60**, and the second insulating film (not illustrated) provided between the charge storage layer **60** and the protruding portion **78**.

The nonvolatile semiconductor storage device **10** according to this embodiment having such a structure provides a nonvolatile semiconductor storage device that has few constraints on miniaturization, is easy to manufacture, and does not require drastic modifications to the peripheral circuit.

Although six semiconductor layers **50** and six gate electrodes **70** are illustrated in FIGS. 1A to 1C, the present invention is not limited thereto. The numbers of semiconductor layers **50** and gate electrodes **70** are arbitrary. Although two of the semiconductor layers **50** are stacked via the insulating layer **55**, the number of stack layers of the semiconductor layer **50** is arbitrary.

In the configuration recited above, the semiconductor layer **50** is periodically arranged with the wide spacing and the narrow spacing. Therefore, it is easy to provide the first insulating film, the charge storage layer **60**, and the second insulating film on the wide spacing (the second spacing) side.

For example, in the case where the semiconductor layers **50** are provided with a single spacing, it is difficult to set aside space to provide the first insulating film, the charge storage layer **60**, and the second insulating film recited above in the spacing therebetween and miniaturize the element. For example, generally, the half pitch F of a nonvolatile semiconductor storage device is established based on the minimum processing dimension of the semiconductor manufacturing step. F is reduced when attempting to increase the bit density of the nonvolatile semiconductor storage device. In such a case, the first insulating film, the charge storage layer **60**, the second insulating film, the protruding portion **78**, the second insulating film, the charge storage layer **60**, and the first insulating film must be provided in a gap having a width of the half pitch F . Therefore, it is extremely difficult to reduce F .

Conversely, in the nonvolatile semiconductor storage device **10** according to this embodiment, the spacing between the semiconductor layers **50** is provided to be the narrow first spacing **51** and the wide second spacing **52**. Thereby, the second spacing **52** can be made larger than the half pitch F of the bit line; and it is relatively easy to set aside space to provide the first insulating film, the charge storage layer **60**, the second insulating film, the protruding portion **78**, the second insulating film, the charge storage layer **60**, and the first insulating film recited above in the gap on the wide second spacing side.

As illustrated in FIGS. 1A to 1C, the spacing between the semiconductor layers **50** includes a portion of a distance $t1$

6

(the first spacing **51**) and a portion of a distance $t2$ (the second spacing **52**) larger than the distance $t1$ alternately arranged. The width of the semiconductor layer **50**, that is, a width $t3$, may essentially be constant.

The semiconductor layer **50** is arranged at a narrow pitch $L1$ and a wide pitch $L2$. Here, narrow pitch $L1 = \text{distance } t1 + \text{width } t3$, and wide pitch $L2 = \text{distance } t2 + \text{width } t3$. A semiconductor layer pair **53** is arranged at a pair pitch $L3$, where the semiconductor layer pair **53** is a pair of semiconductor layers **50** arranged with a spacing of the distance $t1$. At this time, pair pitch $L3 = \text{narrow pitch } L1 + \text{wide pitch } L2 = \text{distance } t1 + \text{distance } t2 + 2 \times \text{width } t3$. Then, a pitch $L4$ of the second spacing **52** is equal to the pair pitch $L3$.

The first spacing (the distance $t1$) may be provided at a period of $4F$, where F is the half pitch of the bit line of the nonvolatile semiconductor storage device **10**. The second spacing (the distance $t2$) also may be provided at a period ($L4$) of $4F$. The semiconductor layer pair **53** also may be provided at a period of $4F$. In other words, the pair pitch $L3$ recited above may be $4F$.

At this time, the spacing, i.e., the distance $t1$, between the pair of the semiconductor layers **50** forming the semiconductor layer pair **53** may be set smaller than F . The spacing, i.e., the distance $t2$, between adjacent semiconductor layer pairs **53** may be set larger than F .

However, the nonvolatile semiconductor storage device **10** according to this embodiment is not limited thereto. It is sufficient that the semiconductor layer pair **53** is provided at the period of $4F$, the distance $t2$ is set larger than F , and the charge storage layer **60** is disposed between the semiconductor layer pairs **53** having a spacing of the distance $t2$, that is, on the second spacing **52** side.

Similar to the semiconductor layer **50**, the gate electrode **70** aligning in the second direction also may be formed such that the spacing between the gate electrodes **70** has a narrow portion and a wide portion. Thereby, a connection portion between the gate electrode **70** and the peripheral circuit, for example, may be provided on the wide spacing side to easily provide a connection. Hereinbelow, the description assumes the case where the gate electrode **70** is provided at a single period, that is, an example in which the distance $L7$ is $2F$.

The half pitch F of the nonvolatile semiconductor storage device **10** according to this embodiment will now be described. Hereinbelow, the description assumes that the same half pitch is used in both the X-axis direction and the Y-axis direction.

FIG. 2 is a schematic plan view illustrating the half pitch of the nonvolatile semiconductor storage device according to the first embodiment of the present invention.

In the nonvolatile semiconductor storage device **10** according to this embodiment illustrated in FIG. 2, the semiconductor layer pair **53** formed by two semiconductor layers **50** juxtaposed with the narrow first spacing **51** ($t1$) is juxtaposed at the pair pitch $L3$, that is, the period of $4F$. On the other hand, the gate electrode **70** is juxtaposed at a period of $2F$.

As illustrated in FIG. 2, one memory cell **80a** corresponds to a portion where one semiconductor layer **50a** and one gate electrode **70a** intersect. Now focusing on the memory cell **80a** including a charge storage layer provided between a side face of the semiconductor layer **50a** and a side face of the gate electrode **70a**, an occupied surface **81a** occupied by the memory cell **80a** has a surface area S . In this case, as illustrated in FIG. 2, four memory cells **80b**, **80c**, **80d**, and **80e** are adjacent to the memory cell **80a**. The memory cells **80b**, **80c**, **80d**, and **80e** also have occupied surfaces **81b**, **81c**, **81d**, and **81e** that have the same surface area S as the memory cell **80a**.

In this case, boundaries between the occupied surface **81a** of the memory cell **80a** and occupied surfaces of memory cells adjacent in the X-axis direction may be, for example, a center line between the semiconductor layer **50a** of the memory cell **80a** and an adjacent semiconductor layer **50b**, and a center line between the semiconductor layer **50a** and another adjacent semiconductor layer **50c**.

Similarly, boundaries between the occupied surface **81a** of the memory cell **80a** and occupied surfaces of adjacent memory cells adjacent in the Y-axis direction may be, for example, a center line between the gate electrode **70a** of the memory cell **80a** and an adjacent gate electrode **70b**, and a center line between the gate electrode **70a** and another adjacent gate electrode **70c**.

The region enclosed by these four center lines may define the occupied surface **81a** of the memory cell **80a**.

In the nonvolatile semiconductor storage device **10**, the period of the semiconductor layer pair **53** is $4F$, and the period of the gate electrode **70** is $2F$, and therefore the relationship $2 \times S = 2F \times 4F$, that is, $S = 4F^2$ holds.

A method for constructing the semiconductor layer **50** and the insulating layer **55** thus including a spacing therebetween having a narrow portion and a wide portion will now be schematically described. To simplify the description, the case is illustrated where only two layers of each of the semiconductor layer **50** and the insulating layer **55** are used. Hereinbelow, the case is described where F is 25 nm.

FIGS. **3A** to **3E** are schematic cross-sectional views in order of the steps, illustrating main components of a method for manufacturing the nonvolatile semiconductor storage device according to the first embodiment of the present invention.

First, as illustrated in FIG. **3A**, two alternating layers of a semiconductor layer film **59** which forms the semiconductor layers **50** and an insulating layer film **55a** which forms the insulating layers **55**, a CVD-deposited silicon oxide film **85** which forms a hard mask, and a silicon nitride film **86** are formed on the substrate **40**. Lithography is used to form a resist mask pattern **87** having a pitch of $L3$ (equal to $4F$, that is, 100 nm) and a width $W1$ of, for example, 30 nm.

As illustrated in FIG. **3B**, hot phosphoric acid processing is performed on the silicon nitride film **86**, and the silicon nitride film **86** is slimmed (its profile is reduced) and patterned to a width $W2$ of, for example, 15 nm.

Then, as illustrated in FIG. **3C**, an amorphous silicon film **89** is formed on the entire surface of the substrate **40** with a thickness of 20 nm. Reactive ion etching is then performed and the amorphous silicon film **89** is left only on side walls of the silicon nitride film **86**.

Continuing as illustrated in FIG. **3D**, hot phosphoric acid processing is performed to remove the silicon nitride film **86**. The CVD-deposited silicon oxide film **85** is patterned using the amorphous silicon film **89** as a mask.

Then, as illustrated in FIG. **3E**, the amorphous silicon film **89** is removed and a hard mask is formed by the CVD-deposited silicon oxide film **85**. The hard mask is used to pattern the two layers of the semiconductor layer film **59** and the insulating layer film **55a**.

Such a method, i.e., double patterning technology, can form the semiconductor layer **50** and the insulating layer **55** such that a spacing therebetween has a narrow portion and a wide portion. The semiconductor layer pair **53** of the semiconductor layers **50** is arranged at a period of $4F$, i.e., the pair pitch $L3$. The spacing (the distance $t1$) between the pair of the semiconductor layers **50** forming the semiconductor layer pair **53** is smaller than F (15 nm ignoring the conversion difference of the patterning). The width of the semiconductor

layer **50** (the width $t3$) is 20 nm ignoring the conversion difference of the patterning. The spacing (the distance $t2$) between adjacent semiconductor layer pairs **53** is larger than F (45 nm ignoring the conversion difference of the patterning).

Although a structure is illustrated where the semiconductor layer film **59** which forms the semiconductor layers **50** and the insulating layer film **55a** which forms the insulating layers **55** are alternately stacked in two layers to simplify the above description, the number of stacks of the semiconductor layer **50** and the insulating layer **55** is arbitrary. The gate electrode **70** also may have a structure in which a narrow spacing and a wide spacing are periodically arranged using the double patterning technology recited above as necessary.

FIGS. **4A** and **4B** are schematic cross-sectional views illustrating structures of main components of the nonvolatile semiconductor storage device according to the first embodiment of the present invention.

In other words, FIGS. **4A** and **4B** illustrate two examples of structures of the first insulating film, the charge storage layer, and the second insulating film of the nonvolatile semiconductor storage device according to this embodiment. FIGS. **4A** and **4B** illustrate enlarged cross sections corresponding to line A-A' of FIG. **1A**.

As illustrated in FIG. **4A**, the charge storage layers **60** are provided between the faces **50v** (the side faces) of the semiconductor layers **50** perpendicular to the major surface **41** on the second spacing **52** side and the face **70v** (the side face) of the gate electrode **70** perpendicular to the major surface **41**. A first insulating film **61** is provided between the semiconductor layers **50** and the charge storage layers **60**. A second insulating film **62** is provided between the charge storage layers **60** and the gate electrode **70**. The first insulating film **61** may function as a tunnel insulating film. The second insulating film **62** may function as a block insulating film. An insulating film **56** is provided between the semiconductor layers **50** on the first spacing **51** side.

In the nonvolatile semiconductor storage device **10** illustrated in FIG. **4A**, the charge storage layers **60** are provided separately for each face **50v** (side face) of the stacked semiconductor layers **50** perpendicular to the major surface **41** on the second spacing **52** side. Thereby, the deterioration of charge retention characteristics due to a lateral diffusion of the charge in the charge storage layer **60**, from a cell to which the charge is written, to an unwritten cell or into other films can be inhibited.

In another nonvolatile semiconductor storage device **11** of this embodiment illustrated in FIG. **4B**, the charge storage layer **60** is continuously provided along the faces **50v** (the side faces) of the stacked semiconductor layers **50** perpendicular to the major surface **41** on the second spacing **52** side and faces **55v** (side faces) of the stacked insulating layers **55** perpendicular to the major surface **41** on the second spacing **52** side. The faces **55v** (the side faces) of the stacked insulating layers **55** perpendicular to the major surface **41** on the second spacing **52** side are provided recessed toward the first spacing **51** side as viewed from the second spacing **52** than are the faces **50v** (the side faces) of the stacked semiconductor layers **50** perpendicular to the major surface **41** on the second spacing **52** side. In other words, the charge storage layer **60** is continuously provided from the side faces of the stacked semiconductor layers **50** to the side faces of the adjacent insulating layers **55**; and the side faces of the insulating layers **55** are recessed from the side faces of the semiconductor layers **50**.

In other words, the charge storage layer **60** is formed such that the length of the charge storage layer **60** aligning along

the side faces of the insulating layers **55** between adjacent semiconductor layers **50** (the length aligning in the direction perpendicular to the major surface **41** of the substrate **40**) is longer in comparison with the shortest distance between the memory cells stacked in the direction perpendicular to the major surface **41**.

Thereby, the deterioration of charge retention characteristics due to a lateral diffusion of the charge in the charge storage layer **60**, from a cell to which the charge is written, to an unwritten cell or into other films can be inhibited.

Thus, the nonvolatile semiconductor storage devices **10** and **11** provide good retention characteristics.

In the nonvolatile semiconductor storage devices **10** and according to this embodiment described above, the bit density can be increased by stacking memory cells in both the direction perpendicular and the direction parallel to the substrate. In other words, the integration can be improved without performing miniaturization.

Further, a transistor of each memory cell has an SOI (Silicon on Insulator) structure including a silicon channel on an insulating film. The gate electrode has a strong controllability over the channel and therefore provides resistance to short channel effects and easily enables multi-level storage. In this embodiment in particular, a UT-SOI (Ultra-Thin Silicon On Insulator) structure is used, and therefore a transistor highly resilient to short channel effects can be realized. Therefore, the dominance over the channel is particularly strong, providing the advantage that multi-level storage such as two bits (that is, four values) per cell or three bits (that is, eight values) per cell can easily be realized. In other words, the memory cell including the charge storage layer **60** can retain multi-bit information.

The semiconductor layer pair **53** is formed at the period of **4F**. Thereby, the space necessary to form the stacked films of the MONOS structure is ensured.

Also, the charge storage layer **60** is shielded by the semiconductor layer **50** on the first spacing **51** side and by the gate electrode **70** on the second spacing **52** side. Therefore, an advantage is provided that inter-cell interference causing the threshold voltage shift of the memory cell according to the writing and erasing operations of an adjacent cell can be inhibited.

Moreover, downscaling is easier than by the technology of, for example, JP-A 2007-266143 (Kokai); and the number of stacking layers can be reduced. Different than the technology of JP-A 2007-266143 (Kokai), NAND chains are formed in the direction parallel to the major surface of the substrate **40**. Therefore, the structure of the peripheral circuit can be similar to that of conventional NAND flash memory.

Thus, the nonvolatile semiconductor storage device and the method for manufacturing the same according to this embodiment provide a new structure that has few constraints on downscaling, is easy to manufacture, and does not require drastic modifications to the peripheral circuit.

First and second examples according to the first embodiment are described as follows.

First Example

A nonvolatile semiconductor storage device **20** according to a first example of the present invention is a flash memory using two stacked layers of memory cells having a 22 nm half pitch to realize a cell surface area of 968 nm² corresponding to a nonvolatile semiconductor storage device of a conventional planar cell structure having a 15 nm half pitch.

An insulating layer that separates the substrate **40** and the first semiconductor layer **50** is shared as a gate insulation film

of a peripheral high-voltage circuit. Restated, the gate insulation film of a transistor of the peripheral high-voltage circuit includes a layer which forms an insulating layer between the substrate **40** and the semiconductor layer **50** most proximal to the substrate **40**. Then, polycrystalline silicon is used as the silicon channel of the semiconductor layer **50**. The charge storage layer **60** is formed in the structure illustrated in FIG. **3A**. In other words, the charge storage layer **60** is provided separately for each face **50v** of the stacked semiconductor layers **50** perpendicular to the major surface **41** on the second spacing **52** side. The description assumes the case where the semiconductor layer **50** is a bit line and the gate electrode **70** is a word line.

A method for manufacturing the nonvolatile semiconductor storage device **20** according to this example will now be described.

FIGS. **5A** and **5B** are schematic cross-sectional views illustrating the method for manufacturing the nonvolatile semiconductor storage device according to the first example of the first embodiment of the present invention.

FIG. **5A** is a view of the first step. FIG. **5B** is a view continuing from FIG. **5A**.

FIGS. **6A** and **6B** are views continuing from FIG. **5B**. FIGS. **7A** to **7C** are views continuing from FIG. **6B**. FIGS. **8A** and **8B** are views continuing from FIG. **7C**.

In FIGS. **5A** to **7A** and FIGS. **8A** and **8B**, each view on the left side is a cross-sectional view in the word line (the gate electrode) direction, that is, a cross-sectional view cut along a plane perpendicular to the extension direction of the word line. Each view on the right is a cross-sectional view in the bit line (the semiconductor layer) direction, that is, a view cut along a plane perpendicular to the extension direction of the bit line. FIGS. **7B** and **7C** are enlarged cross-sectional views of main components in the bit line direction. Each view on the left side of FIGS. **5B** to **7A** and FIGS. **8A** and **8B** is a cross-sectional view along line A-A' of the view on the right side.

As illustrated in FIG. **5A**, first, a cell portion and a peripheral high-voltage circuit portion on a semiconductor substrate **101** are recessed a distance of 30 nm by lithography and reactive ion etching. This step resolves the difference in levels resulting from the gate oxide film thicknesses of the high-voltage circuit portion and a low-voltage circuit portion, and is a step performed for normal flash memory as well.

Continuing, a silicon thermal oxide film, which forms a gate oxide film of the high-voltage circuit portion and an inter-layer dielectric film of the cell, is formed with a thickness of 35 nm. A gate oxide film **102** which forms peripheral low-voltage circuit portion transistors is then formed with a thickness of 8 nm. Thereby, the silicon thermal oxide film **103** which forms the gate oxide layer of the high-voltage circuit portion and the inter-layer dielectric film of the cells has a film thickness of 40 nm.

Then, an n-type polycrystalline silicon film **104** which forms a portion of the gate electrode of the peripheral circuit and a first semiconductor layer is formed with a thickness of 30 nm. A silicon oxide film **105** which forms an insulating layer between the first and second semiconductor layers is formed with a thickness of 40 nm. An n-type polycrystalline silicon film **106** which forms a second semiconductor layer is formed with a thickness of 30 nm. A silicon oxide film **107** is formed with a thickness of 20 nm. A silicon nitride film **108** which forms a CMP (Chemical Mechanical Polishing) stopper is formed with a thickness of 50 nm.

Continuing as illustrated in FIG. **5B**, the semiconductor layers are patterned by lithography and reactive ion etching.

11

Here, during the lithography of the cell portion, a semiconductor layer pair **109** is repeatedly formed at a period of 4F=88 nm using side-wall transfer technology.

The width of each of the semiconductor layers is 15 nm. The width of a gap **110** (the first spacing **51**) between adjacent semiconductor layers is 15 nm. The width of a gap **111** (the second spacing **52**) between semiconductor layer pairs is 43 nm. The collective patterning of the memory cells (also referred to as "cells") also makes an isolation trench which forms STI (Shallow Trench Isolation) of the peripheral circuit portion.

Continuing, the isolation trench of the peripheral circuit portion, the gap **110** between the semiconductor layers, and the gap **111** between the semiconductor layer pairs are filled by an insulating film **112** formed by a TEOS (tetraethoxysilane)/O₃ film or an SOG (Spin On Glass) film, etc.

Then, the insulating film **112** is flattened by CMP.

As illustrated in FIG. 6A, the silicon nitride film **108**, the silicon oxide film **107**, the n-type polycrystalline silicon film **106**, and the silicon oxide film **105** of the peripheral circuit portion and a select gate portion of the first semiconductor layer are then removed by lithography and reactive ion etching. The silicon nitride film **108** and the silicon oxide film **107** of the select gate portion of the second layer are removed by lithography and reactive ion etching.

Continuing, a silicon oxide film **113** which forms the gate oxide film of the select gate and an n-type polycrystalline silicon film **114** which forms the gate electrode of the select gate are formed.

Through-holes are then made through the n-type polycrystalline silicon film **114** and the silicon oxide film **113** of the peripheral circuit portion to the n-type polycrystalline silicon film **104** by lithography and reactive ion etching. An n-type polycrystalline silicon film **115** is then formed.

Thereby, a structure can be formed in which the n-type polycrystalline silicon film **115** and the n-type polycrystalline silicon film **104** are connected in the peripheral circuit portion.

Continuing as illustrated in FIG. 6B, known transistor formation technology is used to pattern the n-type polycrystalline silicon film **115**, the silicon oxide film **113**, and the n-type polycrystalline silicon film **104** of the select gates and the peripheral circuit portion to form gate electrodes **116** of the peripheral circuit, and to form a side wall oxide film **117** and a diffusion layer (not illustrated). An inter-layer dielectric film **118** is filled and flattened.

Then, as illustrated in FIG. 7A, the insulating film **112** in the gap **111** between the adjacent semiconductor layer pairs is etched back by lithography and reactive ion etching.

Side walls of the n-type polycrystalline silicon films **104** and **106** are then cleaned by HF/NH₃ gas. MONOS cells are formed by a stacked insulating film **119**, which includes a silicon thermal oxidation film (having a thickness of 4 nm), a charge storage layer (having a thickness of 5 nm), and a charge block film (having a thickness of 11 nm). Thus, the width of the n-type polycrystalline silicon film which forms the semiconductor layer is 13 nm; and the gap between charge block films is 7 nm. The charge storage layer includes, for example, a silicon nitride film. The charge block film includes, for example, an alumina film.

Continuing, a CVD-deposited WSi film **120** which forms the gate electrode is formed on the entire substrate surface.

The CVD-deposited WSi film **120** is then patterned by lithography and reactive ion etching to form the gate electrodes of the cells.

At this time, the stacked insulating film **119** is collectively patterned to separately provide the charge storage layers in

12

each of the stacked cells. Restated, the silicon nitride film, i.e., the charge storage layer in the stacked insulating film **119**, is oxidized via the insulating film **112**, the silicon thermal oxide film **103**, the silicon oxide film **105**, and the silicon oxide film **107** by a high-temperature rapid thermal oxidation using radicals from a hydrogen/oxygen gas mixture. The charge storage layers are thereby provided separately for the stacked cells.

In other words, prior to the oxidation as illustrated in FIG. 7B, the charge storage layer **121** and the charge block film **122** exist continuously on the side walls of the silicon thermal oxidation film **103**, the silicon oxide film **105**, and the silicon oxide film **107**.

However, as illustrated in FIG. 7C, only the charge storage layer **121** is selectively oxidized by radical oxidation. A silicon thermal oxynitride film **123** is formed, and the charge storage layers **121** can be provided separately for each stacked cell.

Thus, as illustrated in FIG. 8A, a stacked UT-SOI MONOS cell is formed.

Then, an inter-layer dielectric film **124** is formed on the entire substrate surface. Contact plugs **125** are formed to draw out from the peripheral circuit and the stacked semiconductor layers. The elements are connected by leads **126**.

Hereafter, a circuit of the flash memory is formed by multilevel interconnection; but a description thereof is omitted.

Thereby, the nonvolatile semiconductor storage device **20** according to this example illustrated in FIG. 8B is manufactured.

In FIG. 8B, inter-layer dielectric films **127**, **128**, **129**, and **130** are stacked, and leads **134**, **135**, and **136** are connected by contact plugs **131**, **132**, and **133**.

In the structure of the nonvolatile semiconductor storage device **20** of this example, the transistor of each cell has a UT-SOI structure that is resistant to short channel effects and has a strong dominance over the channel. Therefore, an advantage is provided that multi-level storage such as two bits (that is, four values) per cell or three bits (that is, eight values) per cell can easily be realized. Additionally, the charge storage layers of the semiconductor layers forming the pair are shielded by the semiconductor layers themselves, and the charge storage layers of adjacent semiconductor layer pairs are shielded by the control gate electrodes. Therefore, an advantage is provided that inter-cell interference causing the threshold of the cell to vary according to the writing and erasing operations of an adjacent cell can be inhibited.

Moreover, the nonvolatile semiconductor storage device **20** of this example can achieve a storage density twice that of a normal single-layer memory. Although the semiconductor layers are stacked on the substrate in the nonvolatile semiconductor storage device **20**, the patterning of the semiconductor layers (the bit lines) and the gate electrodes (the word lines) can be performed by the same patterning as a normal non-stacked memory, that is, by one lithography step each.

Thus, the nonvolatile semiconductor storage device **20** of this example enables improvement of the integration of cells without miniaturization; and even an advantage is provided that leading-edge lithography steps such as EUV (Extreme Ultraviolet), ArF immersion, and the like are not necessary.

The projected surface area of the cell of the nonvolatile semiconductor storage device **20** of this example is 1,936 nm², and is, for example, about 26% of the surface area in comparison to a cell manufactured by the technology of JP-A 2007-266143 (Kokai).

Further, while the two-layer stacked structure provides an effective cell surface area of 1936/2=968 nm², it is necessary to use an eight-layer stacked structure to realize the same

13

effective cell surface area by the technology of JP-A 2007-266143 (Kokai), resulting in four times the number of stacking layers than that of the nonvolatile semiconductor storage device of this example.

Generally, the yield of a stacked structure is the product of the yield of each layer. Therefore, it is clear that the nonvolatile semiconductor storage device **20** of this example may achieve a higher yield in comparison to that of conventional art.

Although a polycrystalline silicon film and a silicon oxide film are stacked and collectively patterned in the nonvolatile semiconductor storage device **20** of this example, this configuration can be replaced by stacking and collectively patterning an epitaxial silicon film and a silicon oxide film.

Methods for forming the epitaxial silicon film may include a method that uses a portion of the substrate as a seed and forms an epitaxial silicon film at a high temperature. Also, a method may be used that forms an amorphous silicon film and then implements lateral epitaxial growth using a portion of the substrate as a seed. Formation is also possible by forming a stacked film of an epitaxial silicon-germanium film/epitaxial silicon film, selectively etching the epitaxial silicon-germanium film, and performing thermal oxidation of the openings thereof.

Second Example

A nonvolatile semiconductor storage device **21** according to a second example of the present invention is a five-layer stacked memory corresponding to a 10-nm generation half pitch. The nonvolatile semiconductor storage device **21** is an example in which each monocrystalline silicon film forming the semiconductor layers **50** is formed by a stacked film of a monocrystalline silicon film/oxide film formed by sequentially growing stacks of epitaxial silicon and epitaxial silicon-germanium, removing the silicon-germanium film by selective etching, and performing thermal oxidation of the resulting openings.

Although the charge storage layer of the first example is separated by reactive ion etching during the patterning of the gate electrode and thermal oxidation of the charge storage layer, the movement of charge is inhibited in this example by making the length of the charge storage layer **60** between cells in the stacking direction longer than the distance between the stacked cells by forming the insulating films between the stacked semiconductor layers **50** in a three-layer structure. Restated, the nonvolatile semiconductor storage device **21** of this example has the structure schematically illustrated in FIG. 4B.

A method for manufacturing the nonvolatile semiconductor storage device **21** according to this example will now be described.

The method for forming the peripheral circuit and the select gate portion is basically the same even as the number of stacking layers of the semiconductor layers **50** stacked in the direction perpendicular to the major surface **41** of the substrate **40** increases. Therefore, to avoid complexity, only the cell portion is described below. The description assumes that the semiconductor layer **50** is a bit line and the gate electrode **70** is a word line.

FIGS. 9A and 9B are schematic cross-sectional views illustrating the method for manufacturing the nonvolatile semiconductor storage device according to the second example of the first embodiment of the present invention.

14

FIG. 9A is a view of the first step. FIG. 9B is a view continuing from FIG. 9A.

FIGS. 10A and 10B are views continuing from FIG. 9B. FIGS. 11A and 11B are views continuing from FIG. 10B.

These views are cross-sectional views in the bit line (the semiconductor layer) direction, that is, views cut along planes perpendicular to the extension direction of the bit line.

First, as illustrated in FIG. 9A, an epitaxial silicon-germanium film **202** is formed with a thickness of 30 nm on the cell portion of a semiconductor substrate **201**. An epitaxial silicon film **203** with a thickness of 40 nm and an epitaxial silicon-germanium film **204** with a thickness of 30 nm are then formed in ten alternately stacked layers.

Then, a silicon nitride film **205** is formed with a thickness of 100 nm. Lithography and reactive ion etching are used to collectively pattern the silicon nitride film and the multi-layer epitaxial film of the cell region. A CVD silicon oxide film **206** which forms a support of each layer is then formed on the end face of the exposed multi-layer epitaxial film with a thickness of 200 nm.

Continuing as illustrated in FIG. 9B, a slit-shaped through-hole (not illustrated) is made by collectively patterning the silicon nitride film and the multi-layer epitaxial film. The epitaxial silicon-germanium films are removed by selective wet etching from the through-hole.

Then, as illustrated in FIG. 10A, the epitaxial silicon films **203** are oxidized by thermal oxidation to form silicon thermal oxidation films **207** with a thickness of 10 nm. SOG is applied over the entire substrate surface, and an SOG film **208** is filled into the openings between the silicon thermal oxidation films **207**.

As illustrated in FIG. 10B, the semiconductor layers are then patterned by lithography and reactive ion etching similarly to the first example.

Here, semiconductor layer pairs **209** are repeatedly formed at a period of $4F=88$ nm by lithography of the cell portion using side-wall transfer technology. The width of each semiconductor layer in the direction parallel to the substrate is 15 nm. The gap **210** (the first spacing **51**) between the semiconductor layers is 15 nm. The gap **211** (the second spacing **52**) between adjacent semiconductor layer pairs is 43 nm. An isolation trench (not illustrated) which forms an STI of the peripheral circuit portion also is formed by the collective patterning of the cells.

Continuing, an insulating film **212** formed by a TEOS/O₃ film or an SOG film, etc., is filled into the gap **210** between the semiconductor layers and the gap **211** between the semiconductor layer pairs. The insulating film **212** is then flattened by CMP. The insulating film **212** of the gap **211** between adjacent semiconductor layer pairs is then removed by lithography and reactive ion etching.

As illustrated in FIG. 11A, HF wet etching is then used to clean the side walls of the epitaxial silicon film **203** and etch the SOG film **208** into a recessed configuration. At this time, the silicon thermal oxidation film **207** is finer and has a lower wet etching speed in comparison to the SOG film **208**. Therefore, the insulating films on the (second spacing **52**) side between the stacked semiconductor layer pairs have a tapered configuration as illustrated in FIG. 11A.

Continuing as illustrated in FIG. 11B, MONOS cells are formed by a stacked insulating film **213**, which includes a silicon thermal oxidation film (having a thickness of 4 nm), a charge storage layer (having a thickness of 5 nm), and a charge block film (having a thickness of 11 nm). Thus, the width of the n-type polycrystalline silicon film which forms the semiconductor layer is 13 nm; and the gap between charge block films is 7 nm. A CVD-deposited TiN film **214** which forms the gate electrode is then formed over the entire substrate surface.

15

Then, the CVD-deposited TiN film **214** is patterning to form gate electrodes of the cells by lithography and reactive ion etching. Simultaneously, the stacked insulating film **213** is collectively patterned to separately provide the charge storage layers for adjacent cells.

Thus, stacked MONOS cells are formed.

Hereafter, an inter-layer insulating film is formed to fill between the gate electrodes, and multiple layer leads are formed; but a description thereof is omitted.

In the structure of the nonvolatile semiconductor storage device **21** according to this example as well, the transistor of each cell has a UTISOI structure that is resistant to short channel effects and has a strong controllability over the channel. Therefore, an advantage is provided that multi-level storage such as two bits per cell or three bits per cell can easily be realized.

The nonvolatile semiconductor storage device **21** according to this example differs from the first example in that the charge storage layers are not provided separately for each of the stacked semiconductor layers; but the length of the charge storage layer in the stacking direction is longer than the distance between the stacked semiconductor layers. The movement of charge between adjacent cells is thereby inhibited. Therefore, an advantage is provided similarly to the first example that the retention characteristics of the stored charge are excellent.

While the five stacked layers of the nonvolatile semiconductor storage device **21** according to this example provide an effective cell surface area of $1936/5=387\text{ nm}^2$, it is necessary to use nineteen stacked layers to realize a similar effective cell surface area by the technology of, for example, JP-A 2007-266143 (Kokai).

The yield of a stacked structure is the product of the yield of each layer. Therefore, it is clear that the nonvolatile semiconductor storage device **21** according to this example may achieve a high yield in comparison to that of conventional art.

In each of the examples recited above, the method for forming the silicon film which forms the semiconductor layer, the MONOS film structure, the method for processing the MONOS film structure, and the like are not limited to combinations of the structures and the methods described in the first and second examples. Any combination is possible as long as the purport of the present invention is not forfeited.

Further, a polycrystalline silicon film and a monocrystalline silicon film crystallized by laser annealing or a Ni catalyst method, for example, may be used as the channel silicon.

In addition to Al_2O_3 , a metal oxide film such as HfO_2 , La_2O_3 , Pr_2O_3 , Y_2O_3 , ZrO_2 , and the like, and films of multiple combinations thereof can be used as the charge block film (the second insulating film) in the MONOS structure.

In addition to those described in the first and second examples, at least one selected from the group consisting of TaN, W, WSi, TiN, CoSi, NiSi, NiPtSi, PtSi, Pt, Ru, and RuO_2 may be used as the electrode film (a conductive film of at least a portion of the protruding portion **78** of the gate electrode **70** facing the charge storage layer **60**) in the MONOS structure.

FIG. **12** is a graph illustrating characteristics of a nonvolatile semiconductor storage device according to an embodiment of the present invention.

FIG. **12** illustrates a miniaturization roadmap to the half pitch $F=6\text{ nm}$ generation.

In other words, FIG. **12** illustrates the number of stacked layers for the nonvolatile semiconductor storage device of this embodiment to realize the cell surface area of memory cells of conventional art as the half pitch of a flash memory of conventional art changes. Results for the nonvolatile semiconductor storage device of this embodiment with half pitch

16

F of 22 nm and 43 nm are illustrated. The horizontal axis of FIG. **12** represents the half pitch F , and the vertical axis represents the number of stacked layers.

The limitation of downscaling of the nonvolatile semiconductor storage device according to this embodiment is considered to be a half pitch of about 22 nm for the semiconductor layer **50** in the direction parallel to the major surface **41** of the substrate **40**, basically due to constraints of the film thickness of the MONOS film.

Focusing on the case of FIG. **12** where the half pitch F is 22 nm, it is clear that a nonvolatile semiconductor storage device according to this embodiment having not more than ten stacked layers realizes an effective cell surface area corresponding to a conventional single-layer NAND flash memory of the 8-nm generation.

Second Embodiment

A method for manufacturing a nonvolatile semiconductor storage device according to a second embodiment of the present invention is a method for manufacturing a device including the semiconductor layer **50**, the gate electrode **70** provided to face the semiconductor layer **50**, the charge storage layer **60** provided between the semiconductor layer **50** and the gate electrode **70**, the first insulating film **61** provided between the semiconductor layer **50** and the charge storage layer **60**, and the second insulating film **62** provided between the charge storage layer **60** and the gate electrode **70**. The method for forming the semiconductor layer **50**, the gate electrode **70**, and the charge storage layer **60** recited above is distinctive and therefore described in detail.

FIG. **13** is a flowchart illustrating the method for manufacturing the nonvolatile semiconductor storage device according to the second embodiment of the present invention.

In the method for manufacturing the nonvolatile semiconductor storage device according to this embodiment as illustrated in FIG. **13**, first, the semiconductor layer film **59** which forms the semiconductor layers **50** and the insulating layer film **55a** which forms the insulating layers **55** are formed by stacking on the major surface **41** of the substrate **40** (step **S110**). The semiconductor layer film **59** may include, for example, the n-type polycrystalline silicon film or the epitaxial silicon film described in the first and second examples. The insulating layer film **55a** may include, for example, the silicon oxide film or the stacked film of the silicon thermal oxidation film and the SOG film described in the first and second examples.

The semiconductor layer film **59** and the insulating layer film **55a** are patterned (processed) to alternately provide a first spacing **51** and a second spacing **52** larger than the first spacing **51** between stacked units including the semiconductor layers **50** and the insulating layers **55** by using a mask pattern formed by a side wall formed on a side face of a dummy pattern formed parallel to the major surface **41** of the substrate **40** at a period four times the size of the half pitch F of the device to align in a first direction (step **S120**). The method described in FIGS. **3A** to **3E** may be used for this step.

A film which forms the first insulating film **61**, a charge storage layer film which forms the charge storage layer **60**, and a film which forms the second insulating film **62** are formed on a side face of the stacked unit including the semiconductor layers **50** and the insulating layers **55** on the second spacing **52** side; and a gate electrode film which forms the gate electrode **70** is formed on the film which forms the second insulating film and on a major surface of the stacked unit (step **S130**). The various materials described in the first and second embodiments may be used in this step.

17

The gate electrode film is patterned (processed) into a band configuration parallel to the major surface **41** of the substrate **40** to align in the second direction (for example, the Y-axis direction) non-parallel to the first direction (step **S140**).

Thereby, a method for manufacturing a nonvolatile semiconductor storage device having a new configuration can be provided with few constraints on miniaturization, is easy to manufacture, and does not require drastic modifications to the peripheral circuit.

A step that fills an insulating film into the gap on the first spacing **51** side of the patterned (processed) and formed semiconductor layers **50** and the insulating layers **55** may be provided between the step **S120** and the step **S130** recited above.

Third Embodiment

FIG. **14** is a flowchart illustrating a method for manufacturing a nonvolatile semiconductor storage device according to a third embodiment of the present invention.

In the method for manufacturing the nonvolatile semiconductor storage device according to the third embodiment of the present invention illustrated in FIG. **14**, after step **S140** described above in FIG. **13**, the charge storage layer film is provided separately for each side face (the face **50v** perpendicular to the major surface **41**) of the stacked semiconductor layers **50** on the second spacing **52** side (step **S150**). Alternatively, a side face (the face **55v** perpendicular to the major surface **41**) of the insulating layer **55** on the second spacing **52** side is recessed (recessed toward the first spacing **51** side as viewed from the second spacing **52**) from side faces (the faces **50v** perpendicular to the major surface **41**) of the adjacent stacked semiconductor layers **50** on the second spacing **52** side prior to the step **S130** (step **S125**). It is sufficient that either step **S125** or step **S150** recited above is implemented.

In other words, the charge storage layer **60** is provided separately for each stacked memory cell after the step forming the gate electrode **70**; or the insulating layer **55** between the semiconductor layers **50** is recessed to make the length of the charge storage layer aligning along the side faces of the insulating layers **55** in the stacking direction larger than the distance between the stacked memory cells.

The methods described in the first example or the second example can be used for these steps. For example, the step that separately provides the charge storage layer film **69** for each side face (each face **50v** perpendicular to the major surface **41** on the second spacing **52** side) of the stacked semiconductor layers **50** may include the method of selectively oxidizing the charge storage layer film **69** by oxidizing via the stacked insulating layers **55** as described in the first example.

Thereby, the charge storage layer **60** can be essentially divided for each memory cell; and the deterioration of charge retention characteristics due to lateral diffusion of the charge in the charge storage layer **60**, from a cell to which the charge is written, to an unwritten cell or into other films can be inhibited.

It is clear that the embodiments of the present invention described above are applicable to a stacked memory having more stacked layers than the examples recited above. Use of embodiments of the present invention will hereafter enable further continuous improvement of integration. Therefore, various fields of application are expected to expand.

Hereinafter, embodiments of the present invention are described with reference to specific examples. However, the present invention is not limited to these specific examples. For example, one skilled in the art may appropriately select specific configurations of components of the nonvolatile

18

semiconductor storage device and the method for manufacturing the same from known art and similarly practice the present invention. Such practice is included in the scope of the present invention to the extent that similar effects thereto are obtained.

Further, any two or more components of the specific examples may be combined within the extent of technical feasibility; and are included in the scope of the present invention to the extent that the purport of the present invention is included.

Moreover, all nonvolatile semiconductor storage devices and methods for manufacturing the same that can be obtained by an appropriate design modification by one skilled in the art based on the nonvolatile semiconductor storage devices and the methods for manufacturing the same described above as embodiments of the present invention also are within the scope of the present invention to the extent that the purport of the present invention is included.

Furthermore, various modifications and alterations within the spirit of the present invention will be readily apparent to those skilled in the art. All such modifications and alterations should therefore be seen as within the scope of the present invention.

The invention claimed is:

1. A method for manufacturing a nonvolatile semiconductor storage device, the device including: a semiconductor layer; a gate electrode provided facing the semiconductor layer; a charge storage layer provided between the semiconductor layer and the gate electrode; a first insulating film provided between the semiconductor layer and the charge storage layer; and a second insulating film provided between the charge storage layer and the gate electrode, the method comprising:

stacking to form a semiconductor layer film and an insulating layer film on a major surface of a substrate, the semiconductor layer film forming the semiconductor layer, the insulating layer film forming an insulating layer;

processing the semiconductor layer film and the insulating layer film to alternately provide a first spacing and a second spacing larger than the first spacing between stacked units, by using a side wall as a mask pattern, the side wall being formed on a side face of a dummy pattern [formed at a period four times a size of a half pitch **F** of the bit line of the device], the side wall aligning in a first direction parallel to the major surface, the stacked units including the semiconductor layer and the insulating layer;

forming a film forming the first insulating film, a film forming the charge storage layer, and a film forming the second insulating film on a side face of the stacked unit on the second spacing side, and further forming a gate electrode film forming the gate electrode on the film forming the second insulating film and on a major surface of the stacked unit; and

processing the gate electrode film into a band configuration aligning in a second direction parallel to the major surface and non-parallel to the first direction;

wherein the charge storage layer film is separated for each side face of the stacked semiconductor layer on the second spacing side after the processing the gate electrode;

wherein the separating the charge storage layer film includes selectively oxidizing the charge storage layer film by oxidizing via the stacked insulating layer.

2. The method according to claim **1**, wherein a side face of the insulating layer on the second spacing side is recessed

19

from a side face of the adjacent stacked semiconductor layer on the second spacing side prior to the processing the gate electrode.

3. A method for manufacturing a nonvolatile semiconductor storage device, the device including: a semiconductor layer; a gate electrode provided facing the semiconductor layer; a charge storage layer provided between the semiconductor layer and the gate electrode; a first insulating film provided between the semiconductor layer and the charge storage layer; and a second insulating film provided between the charge storage layer and the gate electrode, the method comprising:

stacking to form a semiconductor layer film and an insulating layer film on a major surface of a substrate, the semiconductor layer film forming the semiconductor layer, the insulating layer film forming an insulating layer;

processing the semiconductor layer film and the insulating layer film to alternately provide a first spacing and a second spacing larger than the first spacing between stacked units, by using a side wall as a mask pattern, the side wall being formed on a side face of a dummy pattern [formed at a period four times a size of a half pitch F of the bit line of the device], the side wall aligning in a first direction parallel to the major surface, the stacked units including the semiconductor layer and the insulating layer;

forming a film forming the first insulating film, a film forming the charge storage layer, and a film forming the

20

second insulating film on a side face of the stacked unit on the second spacing side, and further forming a gate electrode film forming the gate electrode on the film forming the second insulating film and on a major surface of the stacked unit; and

processing the gate electrode film into a band configuration aligning in a second direction parallel to the major surface and non-parallel to the first direction;

wherein the stacking to form the semiconductor layer film and the insulating layer film includes selectively removing an epitaxially grown silicon-germanium film and thermally oxidizing at least a portion of an epitaxially grown silicon film after alternately stacking the epitaxially grown silicon film and the epitaxially grown silicon-germanium film;

wherein the stacking to form the semiconductor layer film and the insulating layer film further includes filling an insulating material between the thermally oxidized epitaxially grown silicon films, the insulating material having an etching rate higher than that of the thermally oxidized epitaxially grown silicon film.

4. The method according to claim 1, wherein the dummy pattern is formed at a period four times a size of a half pitch of the bit line of the device.

5. The method according to claim 3, wherein the dummy pattern is formed at a period four times a size of a half pitch of the bit line of the device.

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